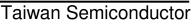
HERAF1001G - HERAF1008G





10A, 50V - 1000V High Efficient Rectifier

FEATURES

- AEC-Q101 qualified available
- Glass passivated chip junction
- High efficiency, Low V_{F}
- High current capability
- High reliability
- High surge current capability
- UL Recognized File # E-326243
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

APPLICATIONS

- DC to DC converter
- Switching mode converters and inverters
- Freewheeling application

MECHANICAL DATA

- Case: ITO-220AC
- Molding compound meets UL 94V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Mounting torque: 0.56 N·m maximum
- Meet JESD 201 class 2 whisker test
- Polarity: As marked
- Weight: 1.70g (approximately)

KEY PARAMETERS			
PARAMETER	VALUE	UNIT	
I _F	10	А	
V _{RRM}	50 - 1000	V	
I _{FSM}	150	А	
T _{J MAX}	150	°C	
Package	ITO-220AC		
Configuration	Single	die	





PIN 2 O-

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}C$ unless otherwise noted)										
PARAMETER	SYMBOL		HERAF 1002G		HERAF 1004G		HERAF 1006G		HERAF 1008G	UNIT
Marking code on the device		HERAF 1001G	HERAF 1002G	HERAF 1003G	HERAF 1004G	HERAF 1005G	HERAF 1006G	HERAF 1007G	HERAF 1008G	
Repetitive peak reverse voltage	V _{RRM}	50	100	200	300	400	600	800	1000	V
Reverse voltage, total rms value	V _{R(RMS)}	35	70	140	210	280	420	560	700	V
Forward current	I _F	10				А				
Surge peak forward current, 8.3ms single half sine wave superimposed on rated load	I _{FSM}	150				A				
Junction temperature	TJ	-55 to +150			°C					
Storage temperature	T _{STG}				-55 to	+150				°C



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THERMAL PERFORMANCE			
PARAMETER	SYMBOL	ТҮР	UNIT
Junction-to-case resistance	R _{eJC}	2	°C/W

ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER		CONDITIONS	SYMBOL	ТҮР	MAX	UNIT
	HERAF1001G HERAF1002G HERAF1003G HERAF1004G			-	1.0	V
Forward voltage ⁽¹⁾	HERAF1005G	$I_F = 10A, T_J = 25^{\circ}C$	V _F	-	1.3	V
	HERAF1006G HERAF1007G HERAF1008G			-	1.7	V
	Reverse current @ rated V _R ⁽²⁾			-	10	μA
Reverse current @ rated v			I _R	-	400	μA
Junction capacitance	HERAF1001G HERAF1002G HERAF1003G HERAF1004G HERAF1005G	1MHz, V _R = 4.0V	CJ	80	-	pF
	HERAF1006G HERAF1007G HERAF1008G			60	-	pF
Reverse recovery time	HERAF1001G HERAF1002G HERAF1003G HERAF1004G HERAF1005G	IF = 0.5A, IR = 1.0A Irr = 0.25A	t _{rr}	-	50	ns
	HERAF1006G HERAF1007G HERAF1008G			-	80	ns

Notes:

1. Pulse test with PW = 0.3ms

2. Pulse test with PW = 30ms

ORDERING INFORMATION		
ORDERING CODE ⁽¹⁾⁽²⁾	PACKAGE	PACKING
HERAF10xG	ITO-220AC	50 / Tube
HERAF10xGH	ITO-220AC	50 / Tube

Notes:

1. "x" defines voltage from 50V(HERAF1001G) to 1000V(HERAF1008G)

2. "H" means AEC-Q101 qualified



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CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

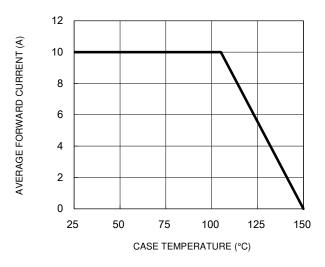
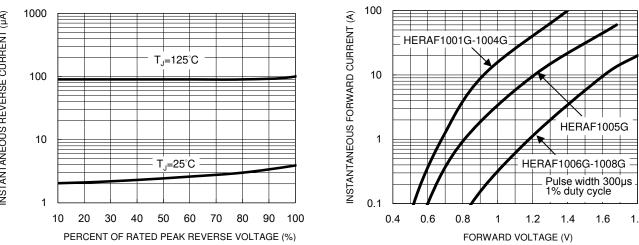


Fig.1 Forward Current Derating Curve

Fig.3 Typical Reverse Characteristics



180 PEAK FORWARD SURGE CURRENT (A) 150 120 90 60 30 0 1 10 100 NUMBER OF CYCLES AT 60 Hz

1000 CAPACITANCE (pF) HERAF1001G-1005G 100 HERAF1006G-1008G 10 f=1.0MHz Vsig=50mVp-p 1 10 100 1 REVERSE VOLTAGE (V)

Fig.4 Typical Forward Characteristics

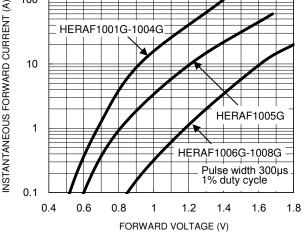


Fig.5 Maximum Non-Repetitive Forward Surge Current

INSTANTANEOUS REVERSE CURRENT (µA)

Fig.2 Typical Junction Capacitance



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CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

50Ω 10Ω trr 🗕 NONINDUCTIVE NONINDUCTIVE ~~ ~~~ +0.5A (-) ± DUT • (+) 50Vdc PULSE 0 GENERATOR (approx) -0.25A (NOTE 2) (-) 1Ω OSCILLOSCOPE 6 (+) (NOTE 1) -1.0A NOTES: 1. Rise Time=7ns max. Input Impedance= 圭 1 megohm 22pf 2. Rise Time=10ns max. Sourse Impedance= 50 ohms

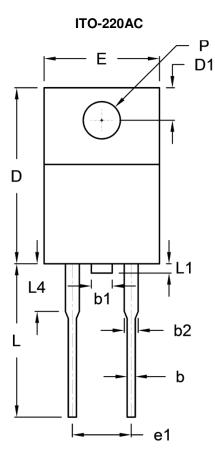
Fig.6 Reverse Recovery Time Characteristic and Test Circuit Diagram

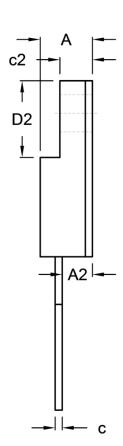


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PACKAGE OUTLINE DIMENSIONS





	DIM. Unit (mm)		Unit ((inch)	
	Min.	Max.	Min.	Max.	
A	4.30	4.70	0.169	0.185	
A2	2.30	2.90	0.091	0.114	
b	0.50	0.90	0.020	0.035	
b1	-	1.80	-	0.071	
b2	0.95	1.45	0.037	0.057	
с	0.46	0.76	0.018	0.030	
c2	2.50	3.10	0.098	0.114	
D	14.80	15.50	0.583	0.610	
D1	2.40	3.20	0.094	0.126	
D2	6.30	6.90	0.248	0.272	
E	9.60	10.30	0.378	0.406	
e1	4.95	5.20	0.195	0.205	
L	12.60	13.80	0.496	0.543	
L1	0.00	1.60	0.000	0.063	
L4	-	4.10	-	0.161	
Р	3.00	3.40	0.118	0.134	

MARKING DIAGRAM



P/N	= Marking Code
G	= Green Compound
YWW	= Date Code
F	= Factory Code



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